

Analog Electronic Circuits (UEC301)

By



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Subject: Analog Electronic Circuits (UEC301)

Faculty name: Dr. Mayank Kumar Rai (Associate Professor & Course Coordinator)

Topic of today's Lecture : Small Signal Model and Operation of BJT-II

Key points

- ✓ Early Effect In BJT
- ✓ Early Effect based Low frequency small signal model of BJT
- ✓ Low frequency small signal operation under the influence of Early effect

Contents of this lecture are based on the following books:

- *Jacob Milman & and C.C.Halkias, “Integrated Electronics Analog and Digital Circuit and Systems” Second Edition.*
- *Adel S. Sedra & K. C. Smith, “MicroElectronic Circuits Theory and Application” Fifth Edition.*
- *Robert L. Boylestad & L. Nashelsky, “Electronic Devices and Circuit Theory” Eleventh Edition.*



Early Effect In BJT

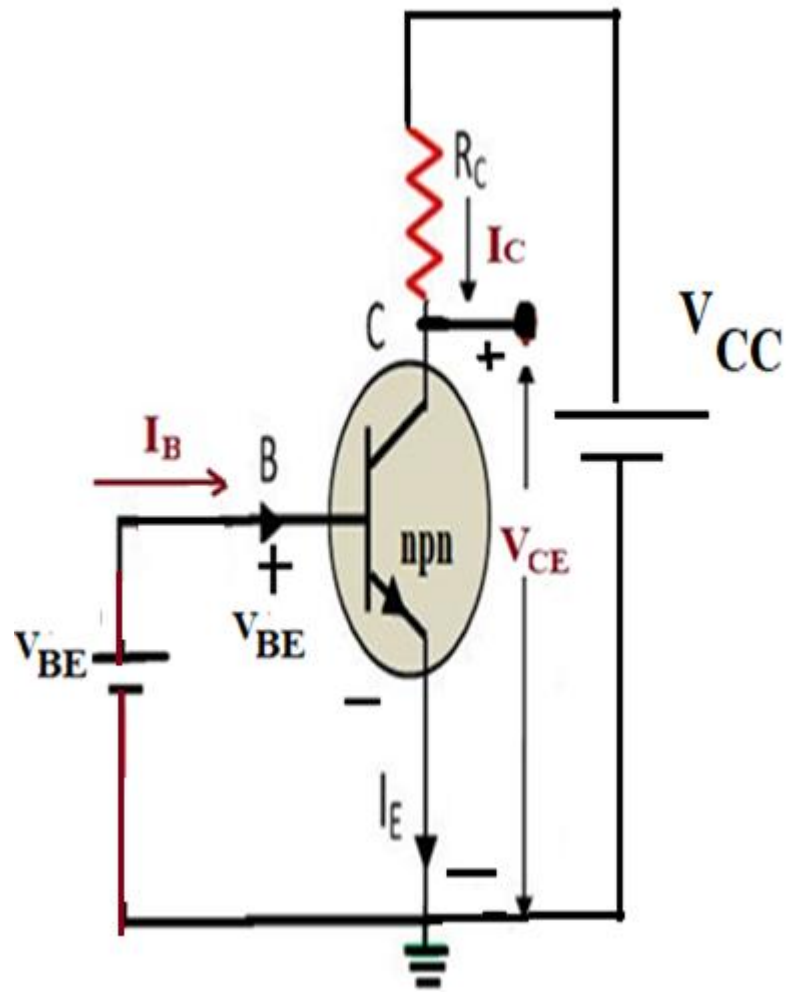


Figure 1: Common emitter configuration based CKT.

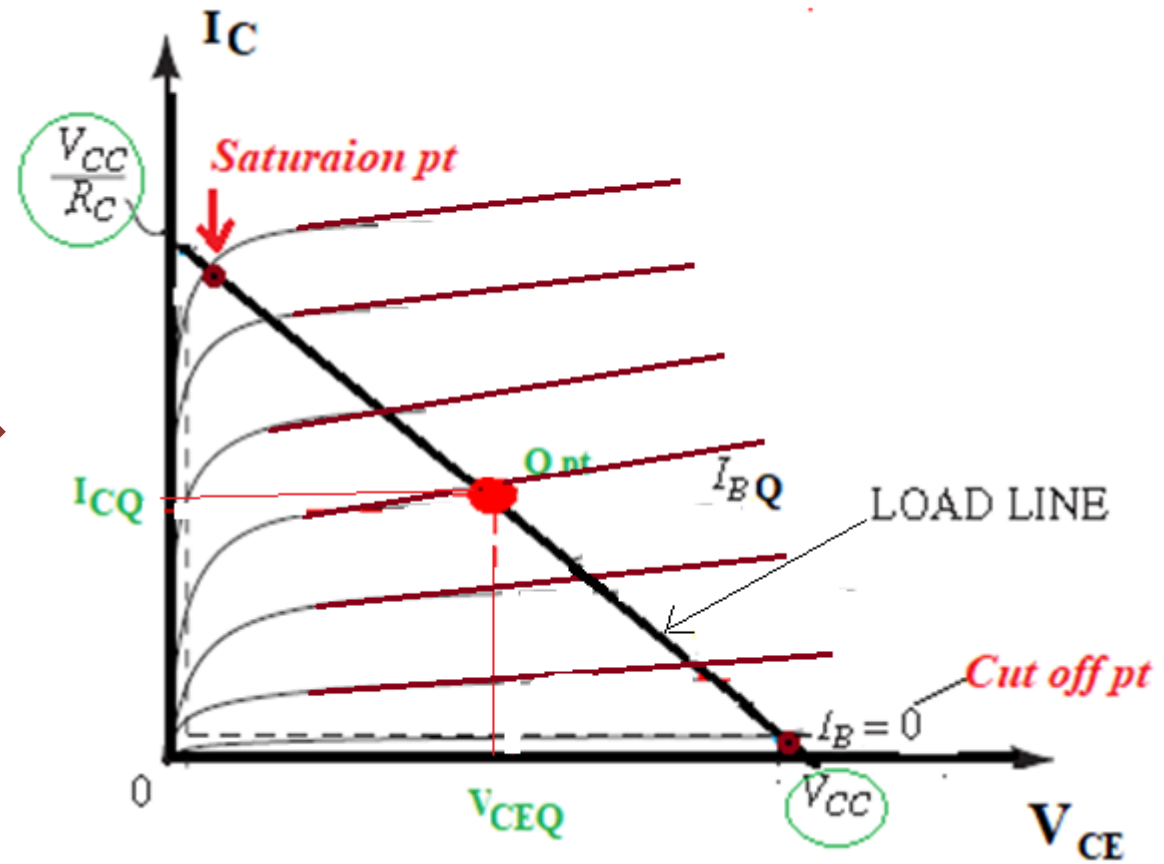
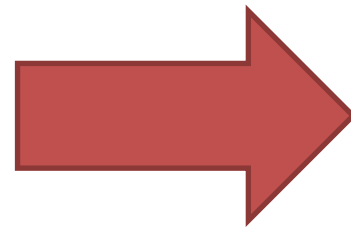


Figure2: Output Char.

Early Effect In BJT

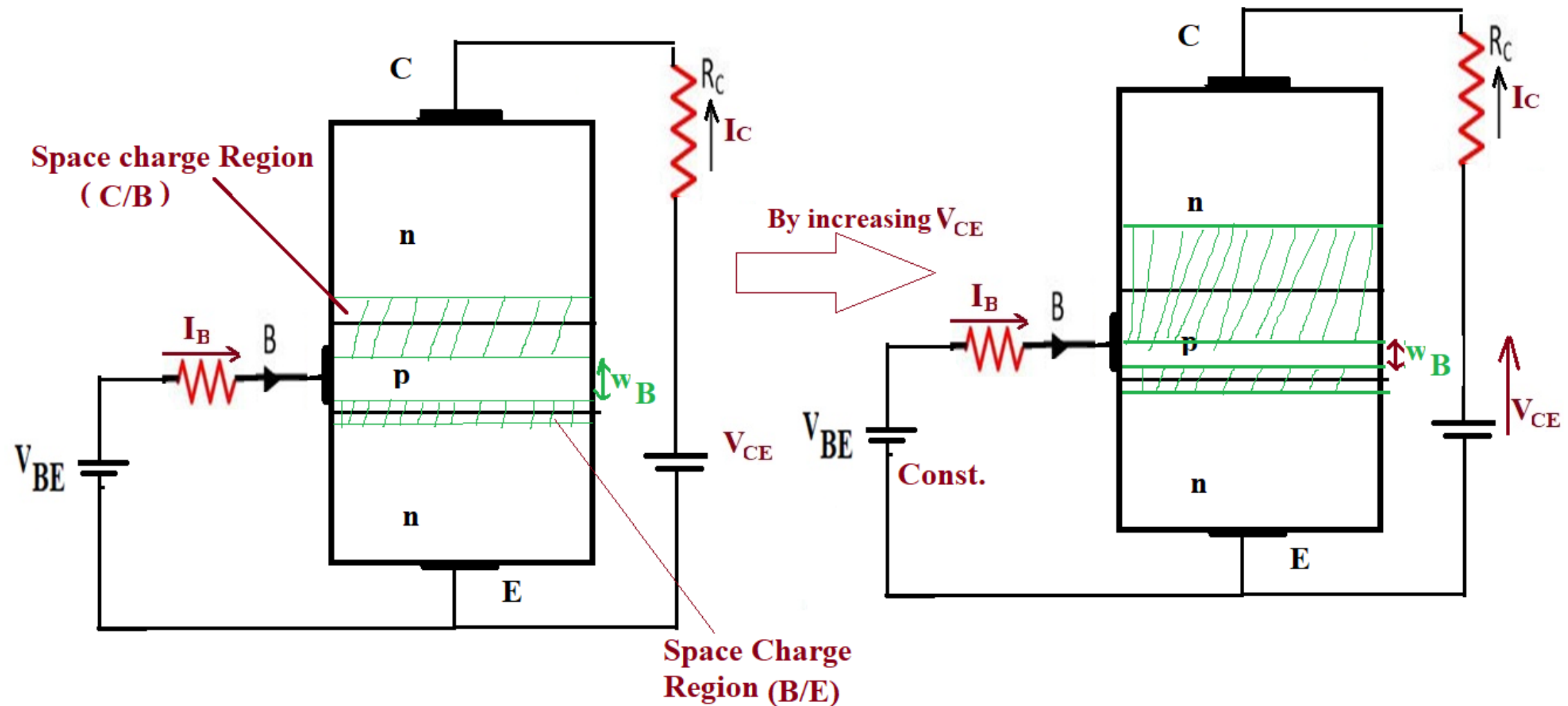
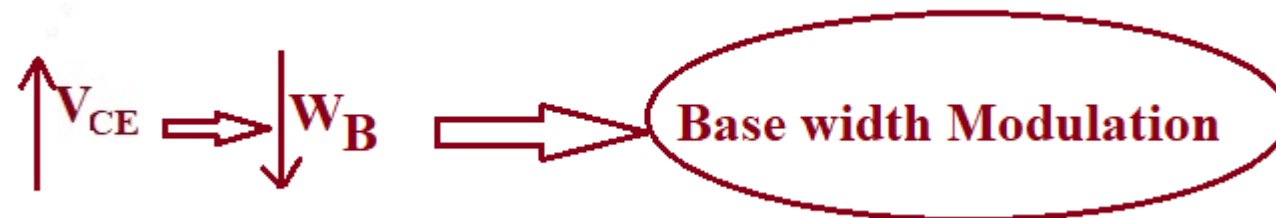
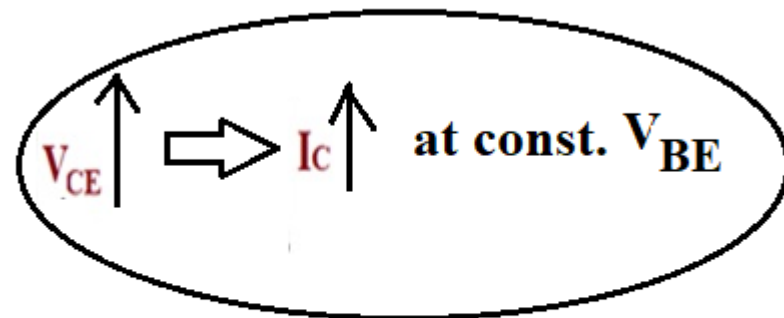


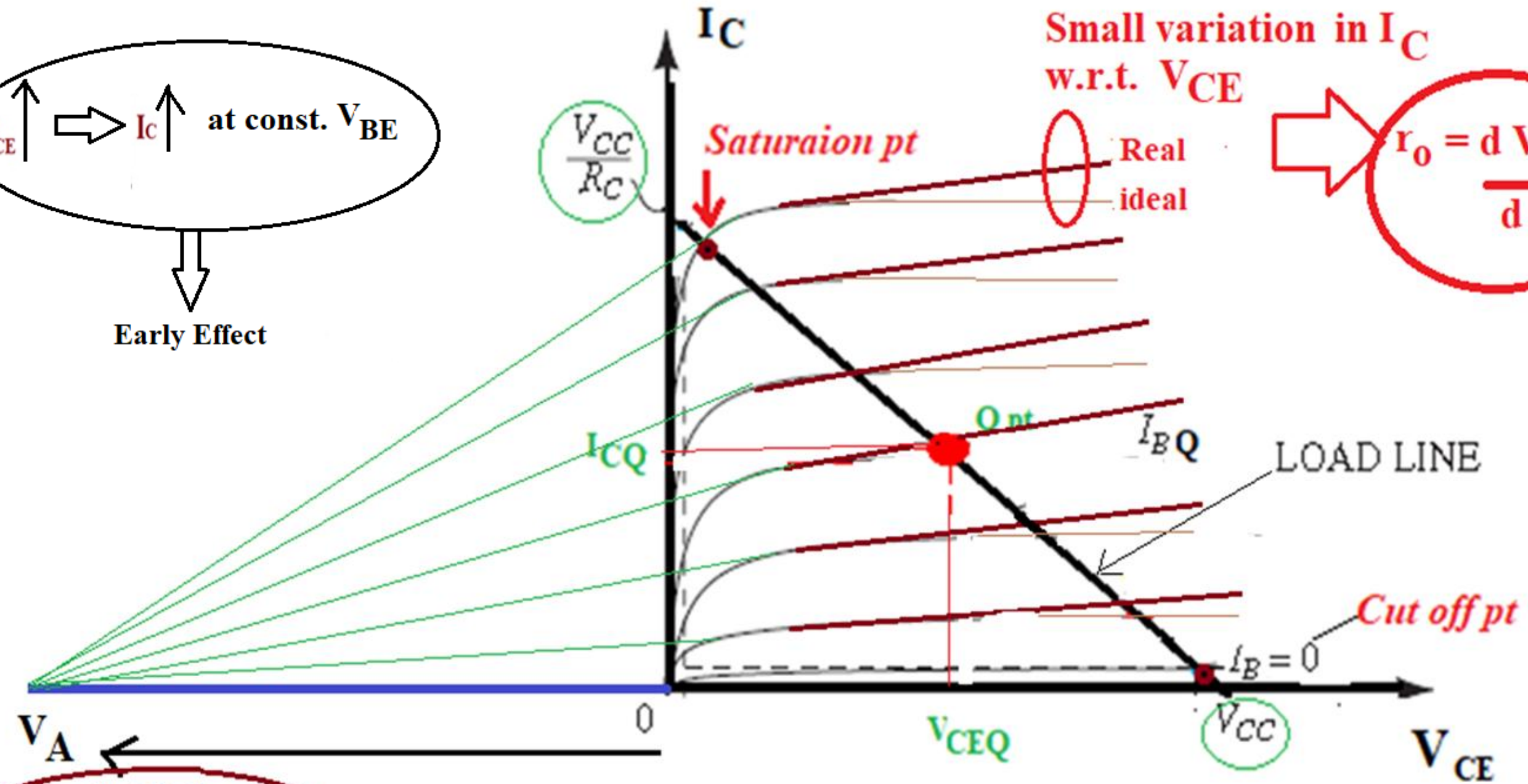
Figure 3: NPN transistor biased in forward active region.



Early Effect.....



Early Effect



$$r_o = \frac{d V_{CE}}{d I_C}$$

Figure 4: Output characteristic including Early effect.



Early Effect.....

Such action causes the effective width of base(W_B) to decrease. This decrease in W_B has two consequences:

- (1) There is less chance for recombination within the base region. Hence α and β increase with an increase in the magnitude of I_C
- (2) The current of minority carriers injected across the emitter junction increases.



Early Effect based Low frequency small signal models of BJT

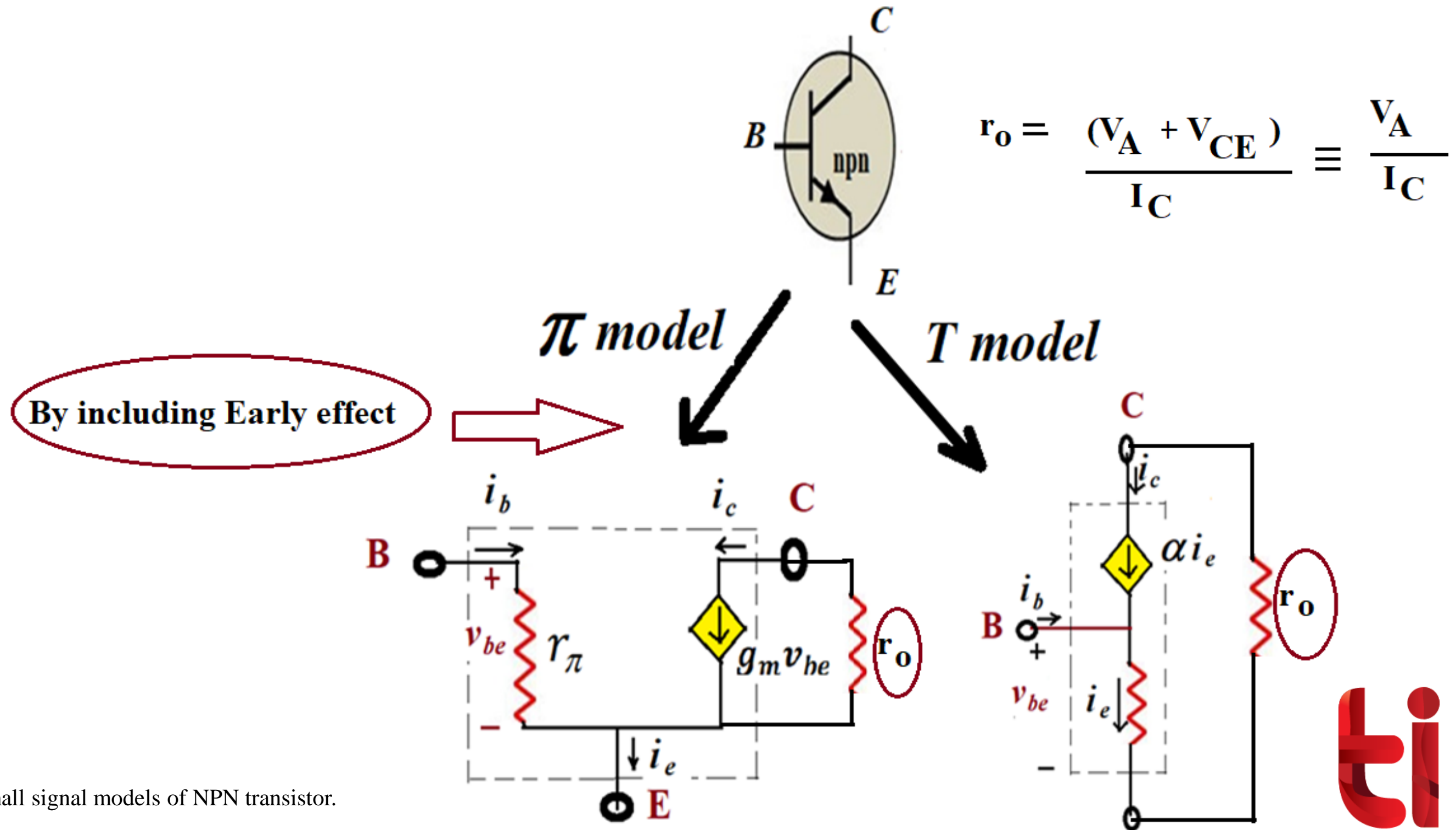


Figure 5: Small signal models of NPN transistor.

Low frequency small signal operation under the influence of Early effect

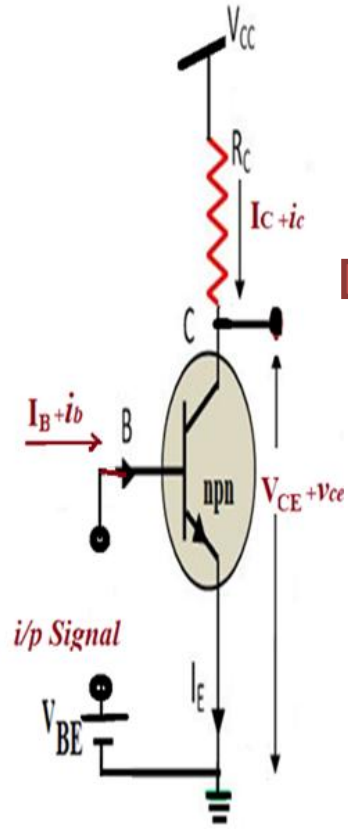


Figure 6: The amplifier CKT.

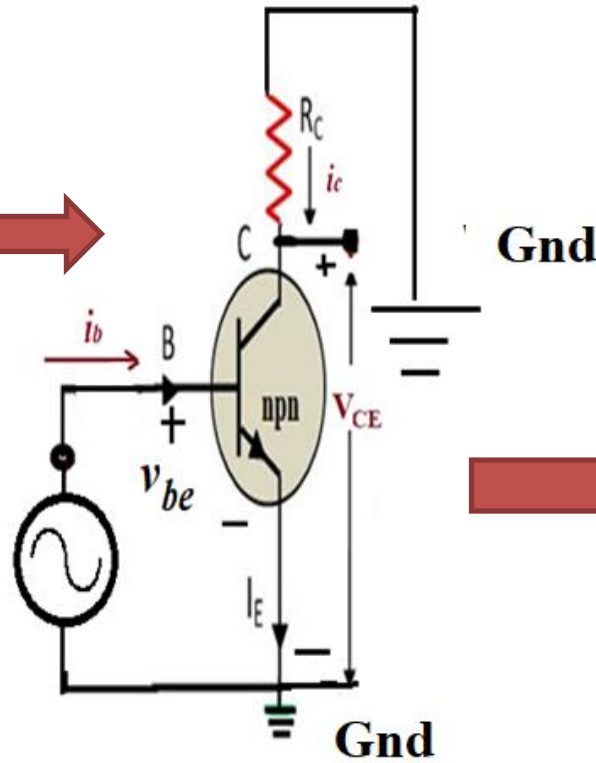


Figure 7: The amplifier CKT with dc sources eliminated.

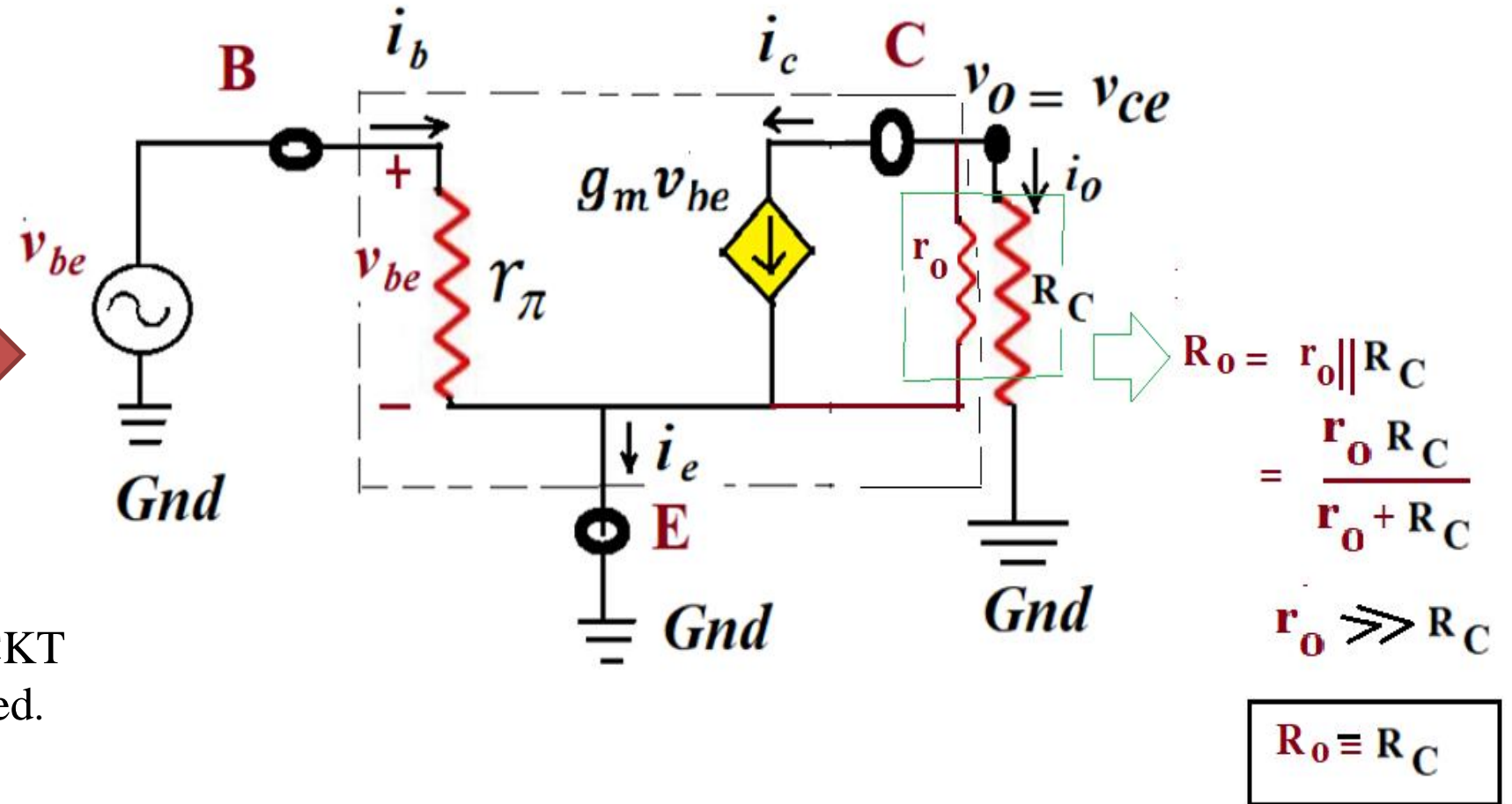


Figure 8: Small signal equivalent CKT of Fig.6.

Voltage gain

$$i_o + i_c = 0$$

$$i_o = -i_c$$

$$v_o = i_o R_o = -i_c (r_o \parallel R_C) \equiv -g_m v_{be} R_C$$

$$\text{Voltage gain, } A_v = \frac{v_{ce}}{v_{be}} \equiv -g_m R_C$$



Thank You

